PROCESS CPD82X

Schottky Diode

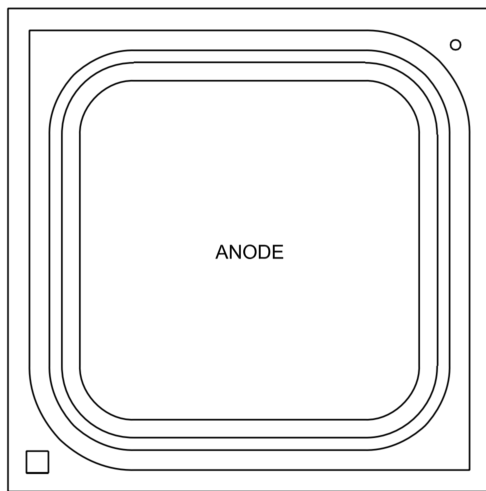
High Current, Low V_F Schottky Diode Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14.6 x 14.6 MILS
Die Thickness	5.5 MILS
Anode Bonding pad Area	11.8 x 11.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



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GROSS DIE PER 4 INCH WAFER
52,965

PRINCIPAL DEVICE TYPES
CMDSH2-3
CMDSH2-4L
CMOSH2-4L
CMUSH2-4L
CMKSH2-4L
CMXSH2-4L

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R0 (20- January 2006)